

## PDB-C609-2

### 42.4mm<sup>2</sup> Active Area Solderable Die Silicon Photodiode

The PDB-609-2 is a 7.0x6.1mm active area solderable die silicon photodiode designed for applications requiring a large active area photodiode with low capacitance and high-speed response time. The device is available with and without flying 32mm long leads and 25mm long buss wire.

Order **PDB-C609-1** for solderable die without leads.

Order **PDB-C609-3** for solderable die with 25mm long buss wire.

### Applications

Optical Encoder

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Position Sensor

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Industrial Controls

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Instrumentation

### Features

Available with and without leads

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Photoconductive

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42.4mm<sup>2</sup> Active Area

## Absolute Maximum Ratings at $T_A=23\text{ }^\circ\text{C}$

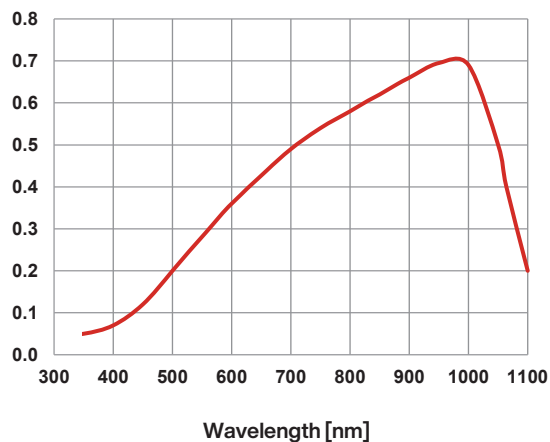
Parameter	Symbol	Min	Max	Unit
Reverse Voltage	$V_R$	-	25	V
Operating Temperature	$T_{OP}$	-40	+100	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-40	+125	$^\circ\text{C}$
Package	Wire on Die			

## Typical Electro-Optical Specifications at $T_A=23\text{ }^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Active Area	-	A.A.	-	42.4	-	$\text{mm}^2$
Active Area Dimensions	-	A.A. <sub>D</sub>	-	6.99x6.07	-	mm
Spectral Range	Spot Scan	$\Delta\lambda$	350	-	1100	nm
Responsivity	$\lambda=950\text{nm}$	$R_\lambda$	0.50	0.70	-	A/W
Capacitance	$V_R=5\text{V}$ , $f=1\text{MHz}$	$C_J$	-	240	-	pF
Dark Current	$V_R=5\text{V}$	$I_D$	-	30	75	nA
Shunt Resistance	$V_R=10\text{mV}$	$R_{SH}$	3	10	-	$\text{M}\Omega$
Noise Equivalent Power	$V_R=0\text{V}$ , $\lambda=950\text{nm}$	NEP	-	$4 \times 10^{-13}$	-	$\text{W}/\sqrt{\text{Hz}}$
Rise Time*	$R_L=1\text{K}\Omega$ , $V_R=50\text{V}$	$t_R$	-	30	-	nS

\*Rise time of 10% to 90% is specified at 660nm

## Typical Spectral Response



## Mechanical Specifications

Units are in inches [mm]

